

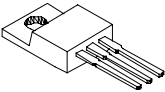
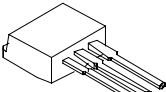
MBR10150CT/MBRB10150CT/MBR10150CT-1
SCHOTTKY RECTIFIER

Applications:

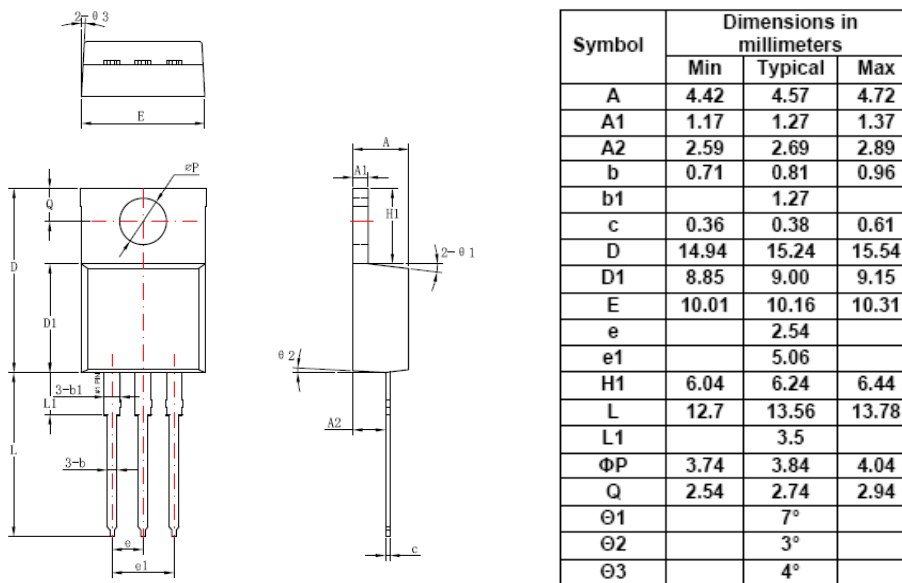
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

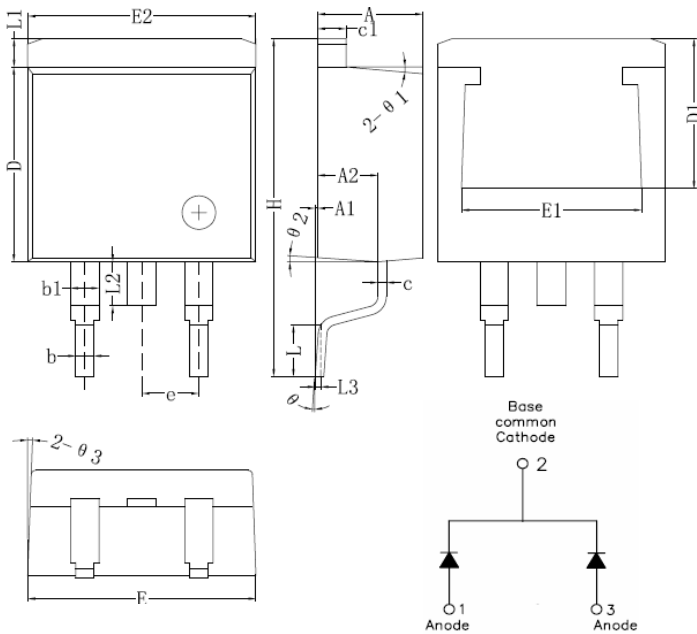
- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Case styles		
MBR10150CT  TO-220AB	MBRB10150CT  D²PAK	MBR10150CT-1  TO-262

Mechanical Dimensions: In Inches / mm

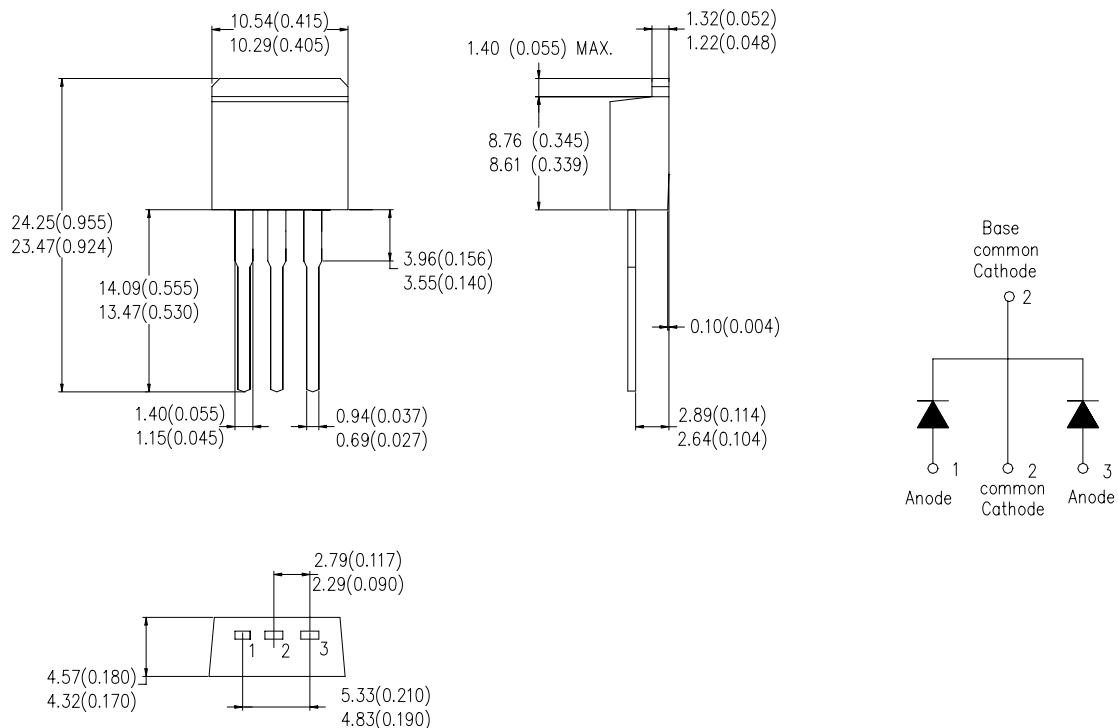


TO-220AB



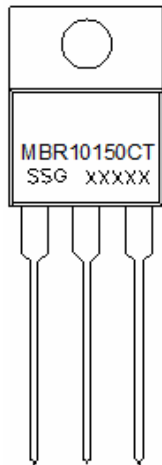
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

D²PAK

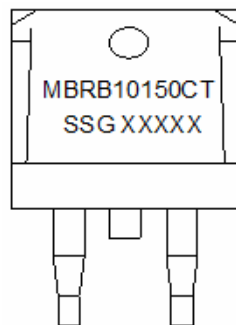


TO-262

Marking Diagram:



MBR10150CT



MBRB10150CT

Where XXXXX is YYWWL

- MBR = Device Type
- B = Package type
- 10 = Forward Current (10A)
- 150 = Reverse Voltage (150V)
- CT/CT-1 = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR10150CT	TO-220AB (Pb-Free)	50pcs / tube
MBRB10150CT	D ² PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C=105^\circ\text{C}$, rectangular wave form	10	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	138	A

Electrical Characteristics:

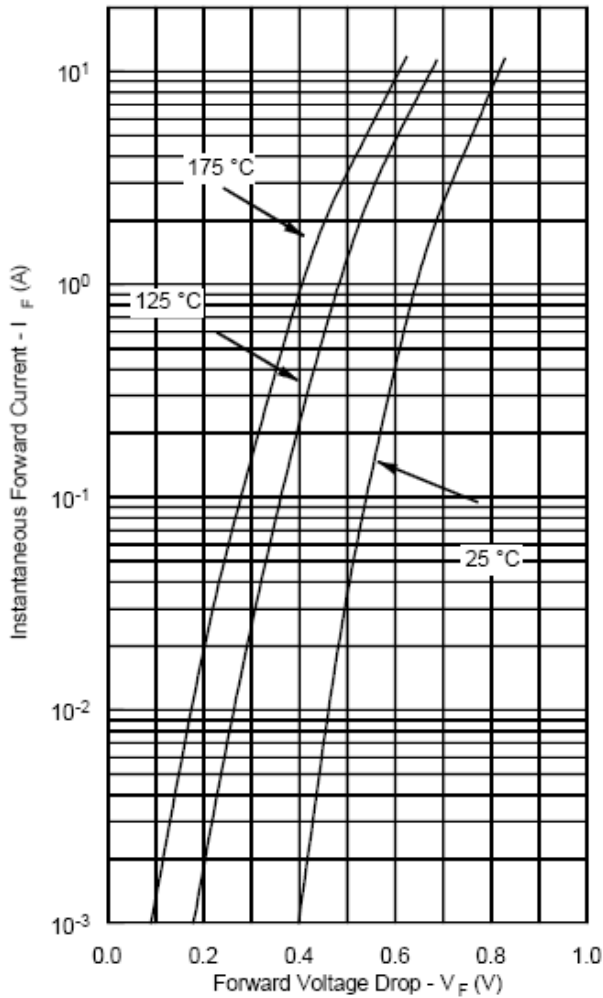
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage	V_{F1}	@ 5A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.93	V
Drop(per leg)*	V_{F2}	@ 5A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.73	V
Max. Reverse Current (per leg)*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.00	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	7.0	mA
Max. Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	200	pF
Typical Series Inductance (per leg)	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

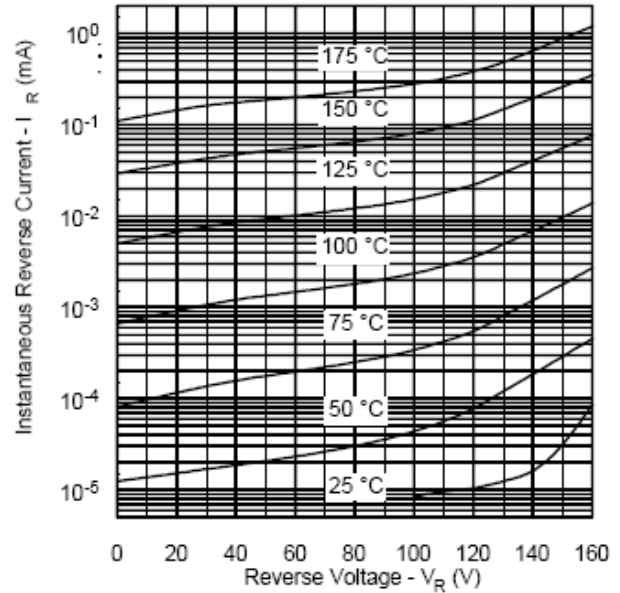
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	4.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	2/1.85	g
Case Style	TO-220AB D ² PAK TO-262			

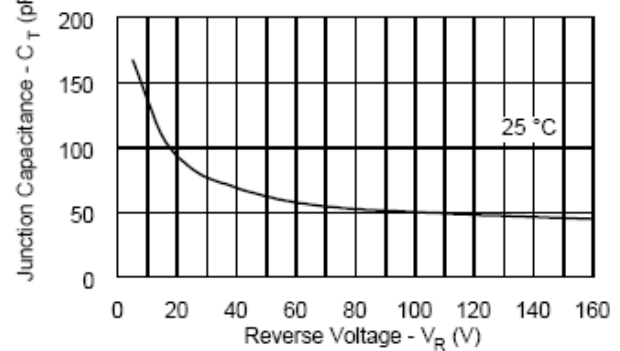
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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